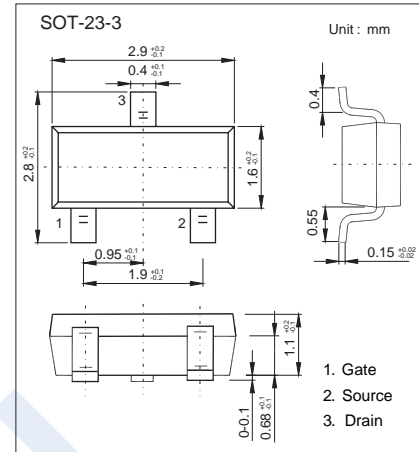
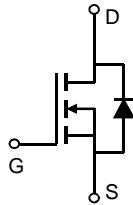


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■ Features

- $V_{DS} (V) = 40V$
- $I_D = 5.8 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 24m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 45m\Omega (V_{GS} = 4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_A=25^\circ C$	A
		$T_A=70^\circ C$	
Pulsed Drain Current	I_{DM}	64	
Power Dissipation	P_D	$T_A=25^\circ C$	W
		$T_A=70^\circ C$	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	$^\circ C/W$
		Steady-State	
Thermal Resistance.Junction- to-Lead	R_{thJL}	80	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μ A, V _{GS} =0V	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1	μA
		V _{DS} =40V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μ A	1.0		2.3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.8A			24	mΩ
		V _{GS} =10V, I _D =5.8A, T _J =125°C			36	
		V _{GS} =4.5V, I _D =4.8A			45	
On State Drain Current	I _{D(ON)}	V _{GS} =4.5V, V _{DS} =5V	64			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5.8A		22		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz		373	448	pF
Output Capacitance	C _{oss}			67		
Reverse Transfer Capacitance	C _{rss}			41		
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.8	2.8	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =5.8A		7.1	11	nC
Total Gate Charge (4.5V)				3.3		
Gate Source Charge	Q _{gs}			1.4		
Gate Drain Charge	Q _{gd}			1.7		
Turn-On DelayTime	t _{d(on)}		V _{GS} =10V, V _{DS} =15V, R _L =2.6Ω, R _G =3Ω		4.5	
Turn-On Rise Time	t _r			2.4		
Turn-Off DelayTime	t _{d(off)}			14.8		
Turn-Off Fall Time	t _f			2.5		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 5.8A, di/dt= 100A/us		10.5	12.6	ns
Body Diode Reverse Recovery Charge	Q _{rr}			4.5		
Maximum Body-Diode Continuous Current	I _S				2.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

* The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	KEA *
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■ Typical Characteristics

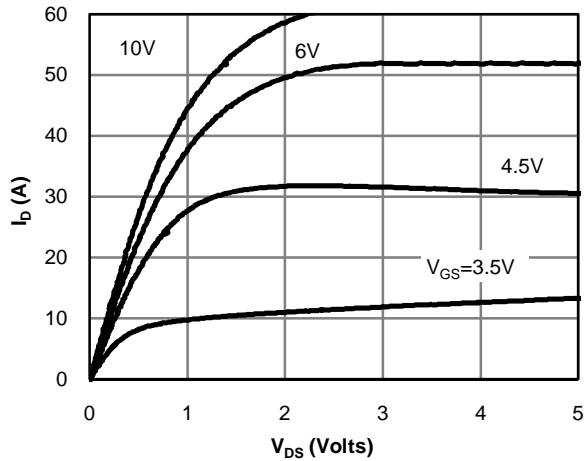


Fig 1: On-Region Characteristics

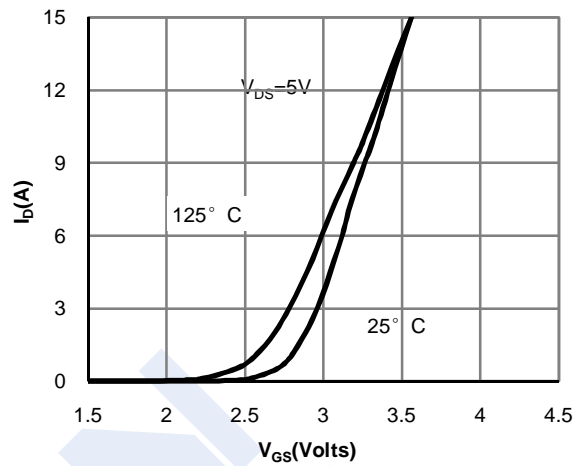


Figure 2: Transfer Characteristics

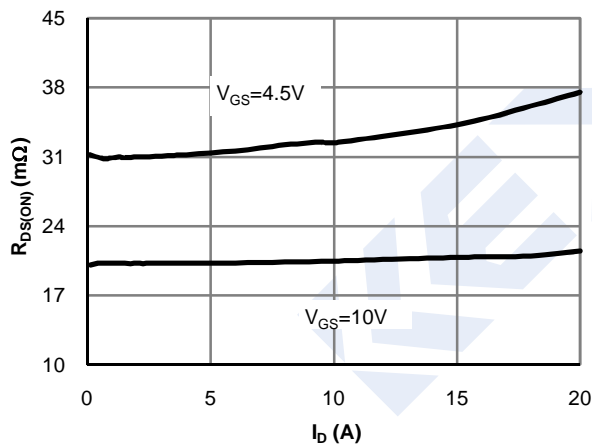


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

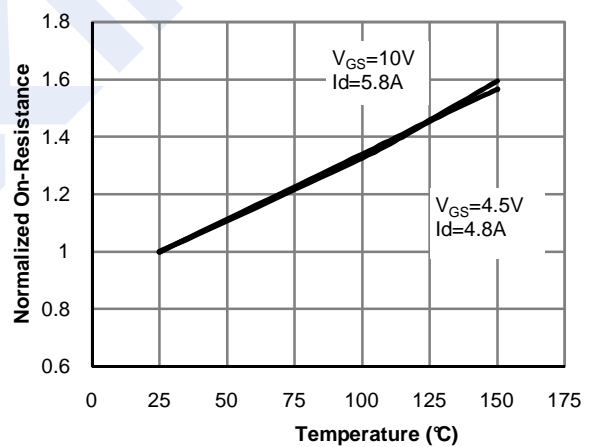


Figure 4: On-Resistance vs. Junction Temperature

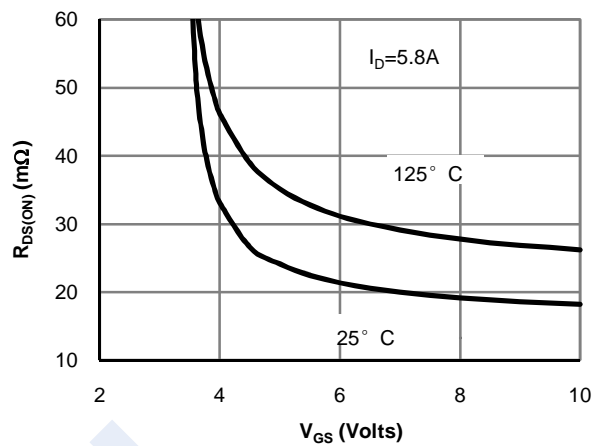


Figure 5: On-Resistance vs. Gate-Source Voltage

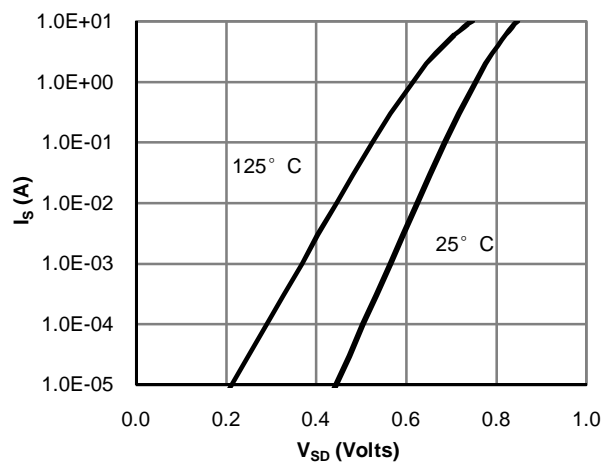


Figure 6: Body-Diode Characteristics

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■ Typical Characteristics

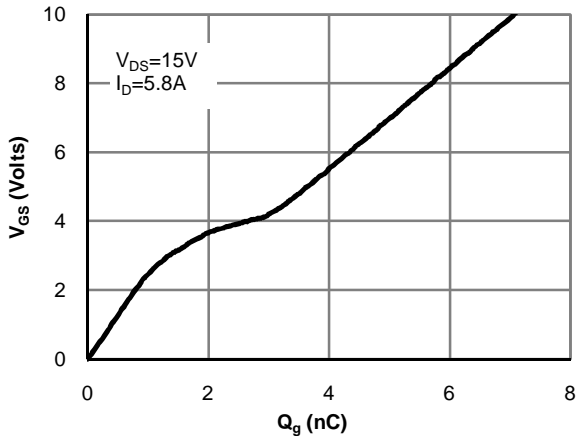


Figure 7: Gate-Charge Characteristics

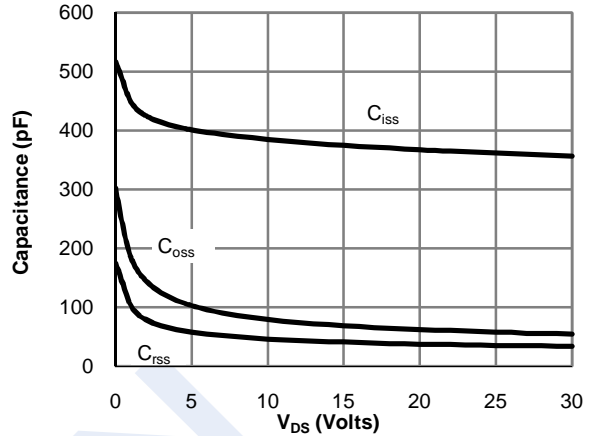


Figure 8: Capacitance Characteristics

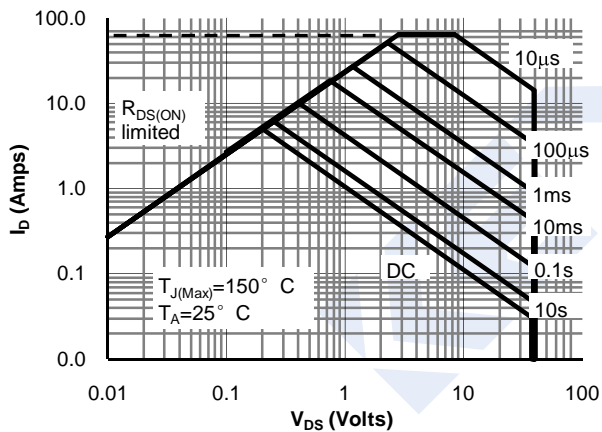


Figure 9: Maximum Forward Biased Safe Operating Area

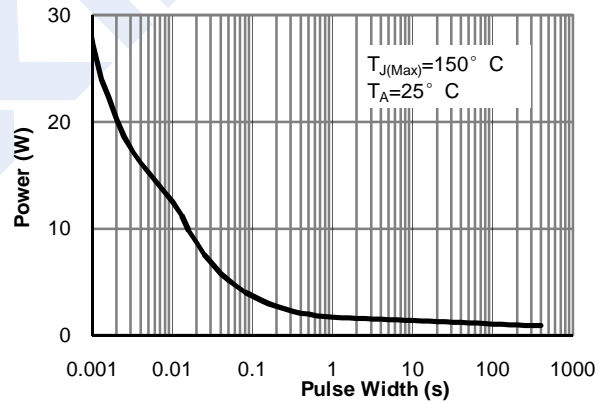


Figure 10: Single Pulse Power Rating Junction-to-Ambient

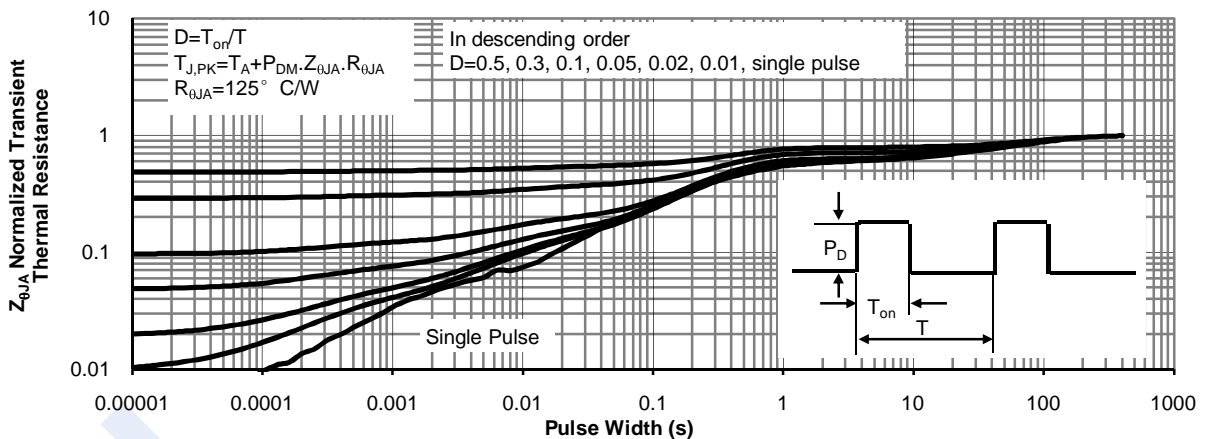


Figure 11: Normalized Maximum Transient Thermal Impedance